

IN THE CLAIMS

Please amend the claims as follows:

1. (Canceled)

2. (Currently amended) A solid-state imaging device comprising:

a first filter unit having a first bandpass wavelength,

the first filter unit including a first upper $\lambda/4$ multilayer film, a first lower $\lambda/4$ multilayer film and a first insulation film sandwiched between the first upper $\lambda/4$ multilayer film and the first lower $\lambda/4$ multilayer film,

a second filter unit having a second bandpass wavelength different from the first bandpass wavelength,

the second filter unit including a second upper $\lambda/4$ multilayer film, a second lower $\lambda/4$ multilayer film and a second insulation film sandwiched between the second upper $\lambda/4$ multilayer film and the second lower $\lambda/4$ multilayer film,

wherein the optical thickness of the first insulation film layer is different from the one of the second insulation film layer,

the upper $\lambda/4$ multilayer film and the lower $\lambda/4$ multilayer film of a first filter unit and the second filter unit have substantially the same center wavelength,

each upper $\lambda/4$ multilayer film and lower $\lambda/4$ multilayer film includes: a first dielectric layer made of a material having a different refractive index from a material forming the first insulation film layer; and a second dielectric layer made of a material having a substantially same refractive index as the material forming the second insulation film layer,

the first dielectric layer is formed so as to be in contact with a main surface of the first insulation film layer, and the second dielectric layer is formed so as to be in contact with a main surface of the first dielectric layer which faces away from the second insulation film layer,

each first dielectric layer has substantially a same optical thickness and each second dielectric layer has substantially a same optical thickness, and

each of the first filter unit and the second filter unit transmits light received by a different light-receiving unit.

3. (Cancelled)

4-19. (Cancelled)

20. (Currently amended) The solid-state imaging device of Claim 2, further including:

a plurality of light-receiving units provided in a semiconductor substrate two-dimensionally,

wherein ~~a wavelength of light received by each of the plurality of light-receiving units is determined based on whether the insulation layer has a portion in correspondence with the light-receiving unit, and, if the insulation layer has the portion, a thickness and/or a material of the portion of the insulation layer,~~

[[the]] each upper and lower $\lambda/4$ multilayer film includes:

a dielectric layer that is positioned most distant from the light-receiving unit being made of a low refraction index material.

21. (Currently amended) The solid-state imaging device of Claim 2, further including:

a protective layer being provided on one of main surfaces of the upper $\lambda/4$ multilayer films ~~film~~, or within the upper $\lambda/4$ multilayer films ~~film~~.

22. (Previously presented) The solid-state imaging device of Claim 20, wherein the protective layer is made of silicon nitride.

23. (Previously presented) The solid state-imaging device of Claim 20, further including:

a light-collecting unit collecting the incoming light, wherein

a portion of the filter unit corresponding to each of the plurality of light-receiving units transmits a wavelength, and

a main surface of the filter unit which faces away from the plurality of light-receiving units is flat.

24. (Currently amended) The solid-state imaging device of Claim 20, wherein

a distance between (i) the plurality of light-receiving unit and (ii) a high refraction index layer which is positioned closest to the plurality of light-receiving units, among two or more high refraction index layers in the upper and lower $\lambda/4$ multilayer films ~~film~~, falls within a range of 1 nm and λ .

25-28. (Cancelled)